HV5036 5.0A 2x36kV --nS

Half Bridge High Voltage Rectifier Assembly

INTRODUCE:

HVGT high voltage silicon rectifier assembly is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

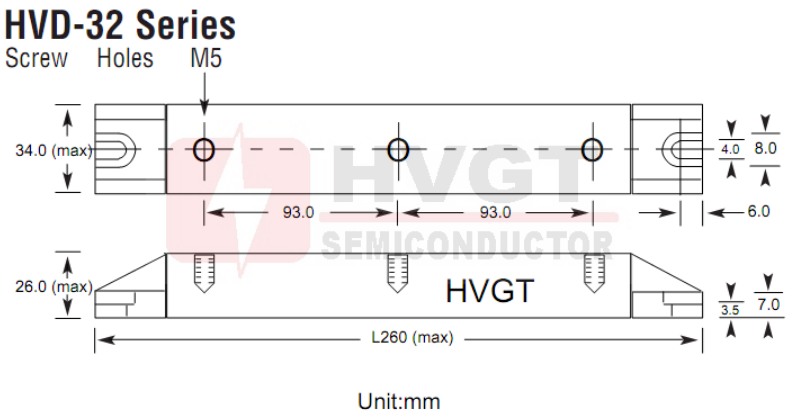
1. High voltage generator.
2. Industrial microwave power supply.
3. High voltage rectifier used in electrostatic cleaning.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: screw holes M5.
3. Net weight: 330.0 grams (approx).

SHAPE DISPLAY:

SIZE: (Unit:mm) **HVGT NAME: HVD-32**



MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value		Units
Repetitive Peak Renerse Voltage	V_{RRM}	T_A=25°C; I_R=1.0uA	36	36	kV
Non-Repetitive Peak Renerse Voltage	V_{RSM}	T_A=25°C; I_R=1.0uA	40	40	kV
Average Forward Current Maximum	I_{FAVM}	T_A=50°C; 50Hz Half-sine Wave; Resistance load	5.0		A
Non-Repetitive Forward Surge Current	I_{FSM}	T_A=25°C; 50Hz Half-Sine Wave; 8.3mS	150		A
Junction Temperature	T_J		150		°C
Allowable Operation Case Temperature	Tc		-40~+150		°C
Storage Temperature	T_{STG}		-40~+150		°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at 25°C; at I_{FAVM}	64	V
Maximum Reverse Current	I_{R1}	at 25°C; at V_{RRM}	5.0	uA
	I_{R2}	at 100°C; at V_{RRM}	50	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	--	nS
Junction Capacitance	C_J	at 25°C; V_R=0V; f=1MHz	--	pF

Fig 1

Forward Current Derating Curve

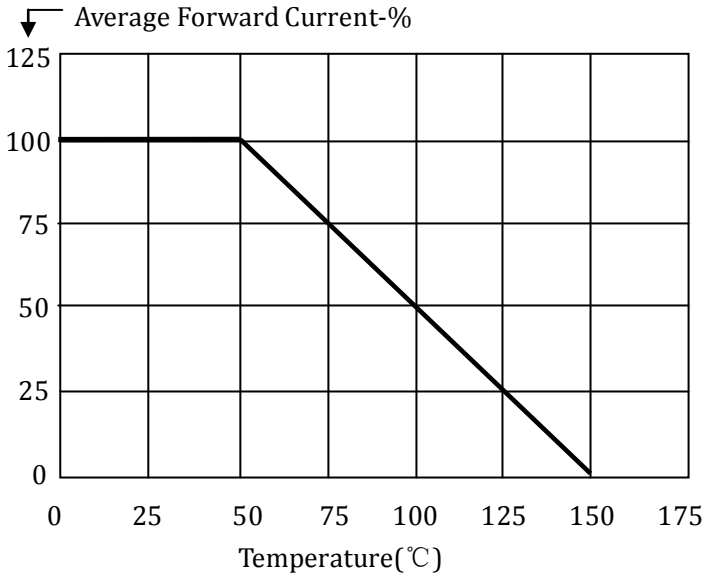
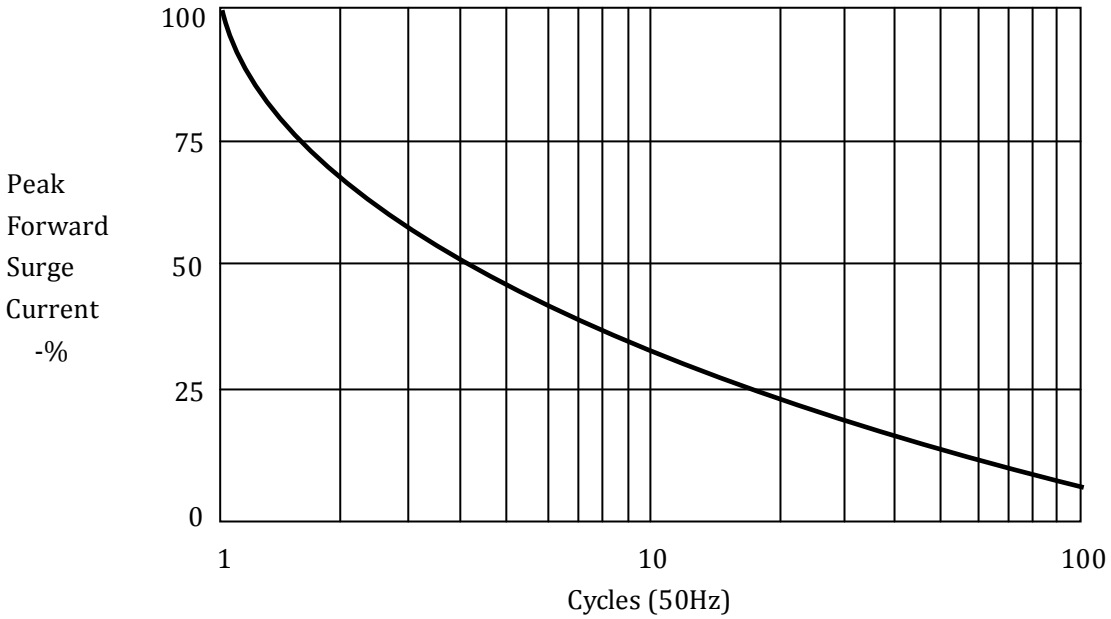


Fig 2

Non-Repetitive Surge Current



Marking	Type	Code	Cathode Mark
	HV5036	HV5036 HVGT